ABSTRACT OF THE DISCLOSURE

A method of forming a local interconnect includes forming an isolation trench within a semiconductor substrate. A first trench isolation material is deposited to within the trench. First isolation material is removed effective to form a line trench into a desired local interconnect. Conductive material is formed therewithin. A second isolation material is deposited over the first isolation material, over the conductive material within the isolation trench and within the line trench. At least some first and second isolation material is removed in at least one common removing step. Integrated circuitry includes a substrate comprising trench isolation material. A local interconnect line is received within a trench formed within the isolation material. The local interconnect includes at least two different conductive materials. One of the conductive materials lines the trench. Another of the conductive materials is received within a conductive trench formed by the one. Other implementations are disclosed.